

DATA SHEET

74F20

Dual 4-input NAND gate

Product specification

1989 Mar 03

IC15 Data Handbook

Dual 4-input NAND gate

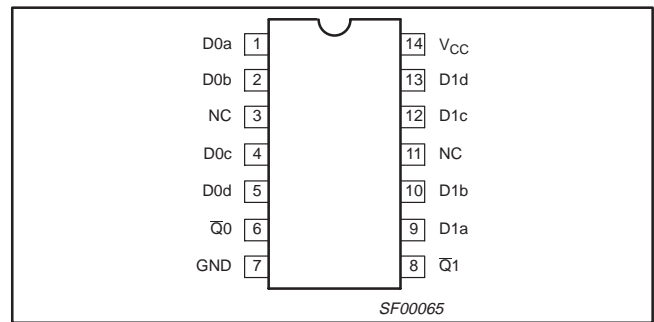
74F20

TYPE	TYPICAL PROPAGATION DELAY	TYPICAL SUPPLY CURRENT (TOTAL)
74F20	3.5ns	2.2mA

ORDERING INFORMATION

DESCRIPTION	COMMERCIAL RANGE $V_{CC} = 5V \pm 10\%$, $T_{amb} = 0^{\circ}C \text{ to } +70^{\circ}C$	PKG DWG #
14-pin plastic DIP	N74F20N	SOT27-1
14-pin plastic SO	N74F20D	SOT108-1

PIN CONFIGURATION

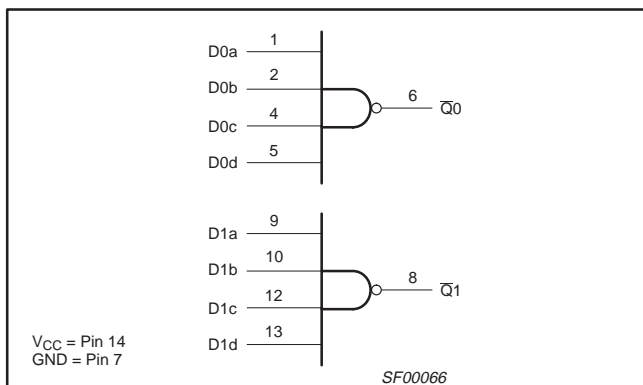


INPUT AND OUTPUT LOADING AND FAN-OUT TABLE

PINS	DESCRIPTION	74F (U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
Dna, Dnb, Dnc, Dnd	Data inputs	1.0/1.0	20 μ A/0.6mA
$\bar{Q}0, \bar{Q}1$	Data outputs	50/33	1.0mA/20mA

NOTE: One (1.0) FAST unit load is defined as: 20 μ A in the High state and 0.6mA in the Low state.

LOGIC DIAGRAM

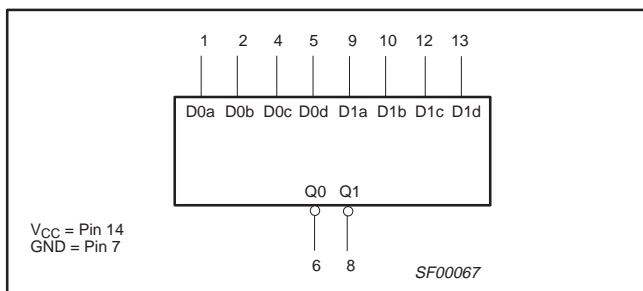


FUNCTION TABLE

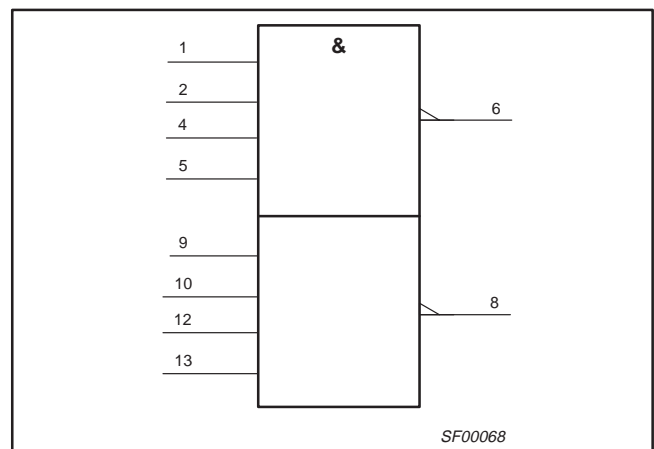
INPUTS				OUTPUT
Dna	Dnb	Dnc	Dnd	$\bar{Q}n$
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

NOTES:
 H = High voltage level
 L = Low voltage level
 X = Don't care

LOGIC SYMBOL



IEC/IEEE SYMBOL



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ABSOLUTE MAXIMUM RATINGS

(Operation beyond the limits set forth in this table may impair the useful life of the device.
Unless otherwise noted these limits are over the operating free-air temperature range.)

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	-0.5 to +7.0	V
V _{IN}	Input voltage	-0.5 to +7.0	V
I _{IN}	Input current	-30 to +5	mA
V _{OUT}	Voltage applied to output in High output state	-0.5 to V _{CC}	V
I _{OUT}	Current applied to output in Low output state	40	mA
T _{amb}	Operating free-air temperature range	0 to +70	°C
T _{stg}	Storage temperature range	-65 to +150	°C

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS			UNIT
		MIN	NOM	MAX	
V _{CC}	Supply voltage	4.5	5.0	5.5	V
V _{IH}	High-level input voltage	2.0			V
V _{IL}	Low-level input voltage			0.8	V
I _{IK}	Input clamp current			-18	mA
I _{OH}	High-level output current			-1	mA
I _{OL}	Low-level output current			20	mA
T _{amb}	Operating free-air temperature range	0		+70	°C

DC ELECTRICAL CHARACTERISTICS

(Over recommended operating free-air temperature range unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS ¹	LIMITS			UNIT	
			MIN	TYP ²	MAX		
V _{OH}	High-level output voltage	V _{CC} = MIN, V _{IL} = MAX	±10%V _{CC}	2.5		V	
		V _{IH} = MIN, I _{OH} = MAX	±5%V _{CC}	2.7	3.4		
V _{OL}	Low-level output voltage	V _{CC} = MIN, V _{IL} = MAX	±10%V _{CC}		0.30	V	
		V _{IH} = MIN, I _{OL} = MAX	±5%V _{CC}		0.30		
V _{IK}	Input clamp voltage	V _{CC} = MIN, I _I = I _{IK}			-0.73	V	
I _I	Input current at maximum input voltage	V _{CC} = MAX, V _I = 7.0V			100	μA	
I _{IH}	High-level input current	V _{CC} = MAX, V _I = 2.7V			20	μA	
I _{IL}	Low-level input current	V _{CC} = MAX, V _I = 0.5V			-0.6	mA	
I _{OS}	Short-circuit output current ³	V _{CC} = MAX		-60		mA	
I _{CC}	Supply current (total)	V _{CC} = MAX	I _{CCH}	V _{IN} = GND	0.9	1.4	mA
			I _{CCL}	V _{IN} = 4.5V	3.4	5.1	

NOTES:

- For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- All typical values are at V_{CC} = 5V, T_{amb} = 25°C.
- Not more than one output should be shorted at a time. For testing I_{OS}, the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting of a High output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

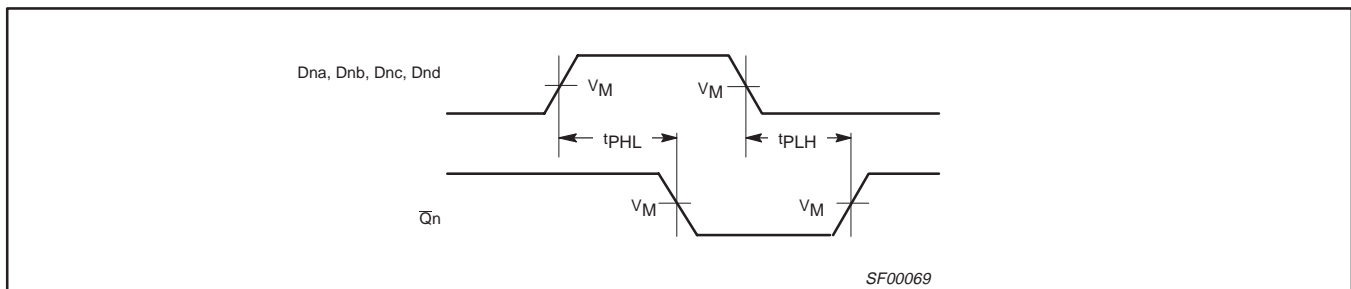
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AC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITION	LIMITS					UNIT
			$V_{CC} = +5.0V$ $T_{amb} = +25^{\circ}C$ $C_L = 50pF, R_L = 500\Omega$			$V_{CC} = +5.0V \pm 10\%$ $T_{amb} = 0^{\circ}C \text{ to } +70^{\circ}C$ $C_L = 50pF, R_L = 500\Omega$		
			MIN	TYP	MAX	MIN	MAX	
t_{PLH} t_{PHL}	Propagation delay Dna, Dnb, Dnc, Dnd to \bar{Q}_n	Waveform 1	2.4 2.0	3.7 3.2	5.0 4.3	2.4 2.0	6.0 5.3	ns

AC WAVEFORMS



Waveform 1. Propagation Delay for Inverting Outputs

NOTE:

For all waveforms, $V_M = 1.5V$.

TEST CIRCUIT AND WAVEFORMS

Test Circuit for Totem-Pole Outputs

DEFINITIONS:

- R_L = Load resistor; see AC ELECTRICAL CHARACTERISTICS for value.
- C_L = Load capacitance includes jig and probe capacitance; see AC ELECTRICAL CHARACTERISTICS for value.
- R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

Input Pulse Definition

family	INPUT PULSE REQUIREMENTS					
	amplitude	V_M	rep. rate	t_w	t_{TLH}	t_{THL}
74F	3.0V	1.5V	1MHz	500ns	2.5ns	2.5ns

SF00006

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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

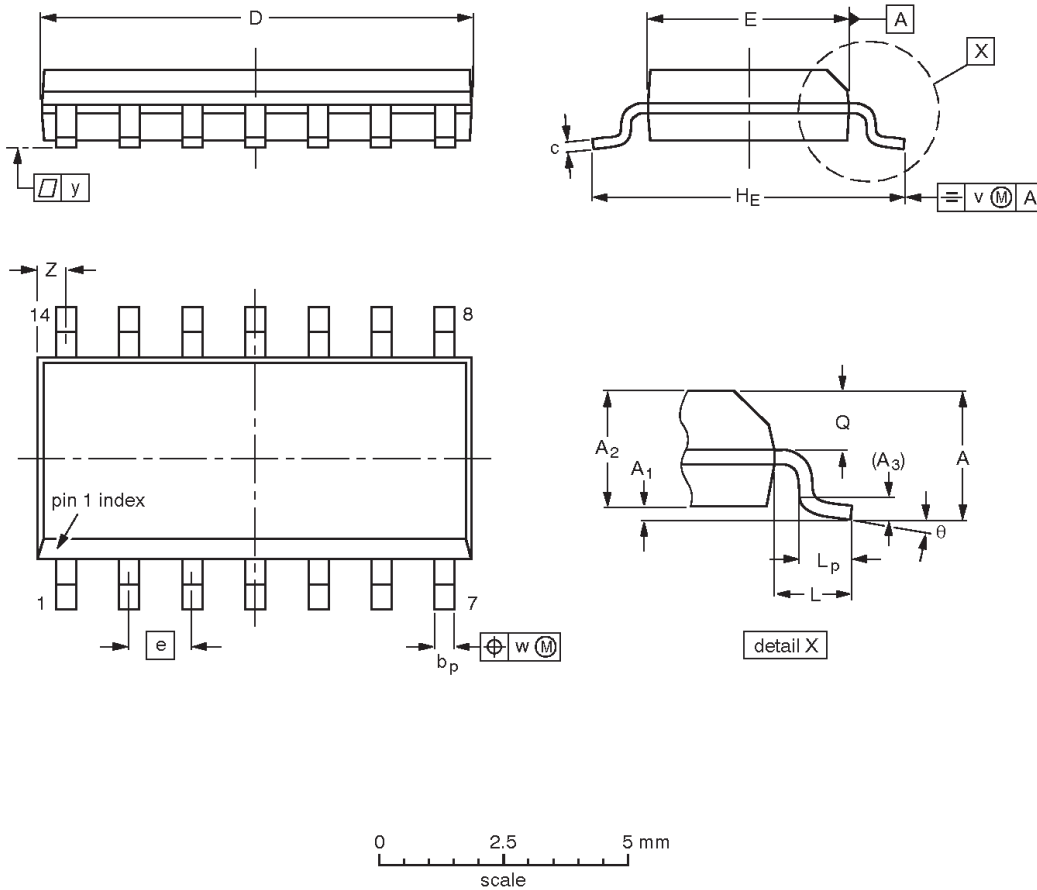
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				95-01-29 97-05-22

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NOTES

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Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
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[1] Please consult the most recently issued datasheet before initiating or completing a design.

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Philips Semiconductors
811 East Arques Avenue
P.O. Box 3409
Sunnyvale, California 94088-3409
Telephone 800-234-7381

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